

UNISONIC TECHNOLOGIES CO., LTD

15N25-P **Preliminary Power MOSFET**

15A, 250V N-CHANNEL **POWER MOSFET**

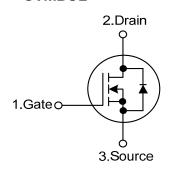
UTC's advanced technology to provide the customers with perfect R_{DS(ON)}, high switching speed, high current capacity and low gate charge.

automotive, high efficiency switching for DC/DC converters and DC motor control, etc.



- * $R_{DS(ON)}$ =0.25 Ω @ V_{GS} =10V, I_{D} =7.5A
- * Low Gate Charge (Typical 33nC)
- * Low C_{RSS} (Typical 25pF)
- * High Switching Speed

SYMBOL

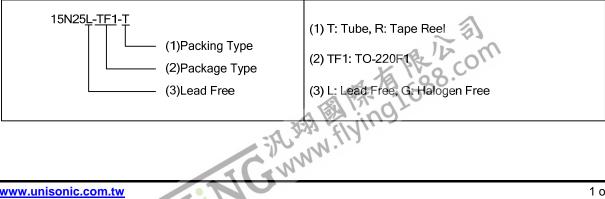


DESCRIPTION The UTC 15N25-P is an N-channel enhancement MOSFET using TO-220F1 The UTC 15N25-P is universally applied in low voltage such as

ORDERING INFORMATION

Ordering Number		Daalaasa	Pin Assignment			Daaldaa	
Lead Free	Halogen Free	Package	1	2	3	Packing	
15N25L-TF1-T	15N25G-TF1-T	TO-220F1	G	D	S	Tube	
15N25L-TF1-R	15N25G-TF1-R	TO-220F1	G	D	S	Tape Reel	

Note: Pin Assignment: G: Gate D: Drain S: Source



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ABSOLUTE MAXIMUM RATINGS (unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	250	V
Gate-Source Voltage		V_{GSS}	±30	V
Continuous Drain Current	Continuous	I_D	15	Α
	Pulsed	I _{DM}	60	Α
Single Pulsed Avalanche Current		I _{AS}	15	Α
Single Pulsed Avalanche Energy		E _{AS}	340	mJ
Power Dissipation		P_{D}	83	W
Junction Temperature		T_J	+150	°C
Storage Temperature		T _{STG}	-55 ~ + 150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT	
Junction to Ambient	θ_{JA}	110	°C/W	
Junction to Case	θ_{JC}	1.5	°C/W	

ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITIONS		TYP	MAX	UNIT	
OFF CHARACTERISTICS			•	•			
Drain-Source Breakdown Voltage	BV _{DSS}	I _D =250μA, V _{GS} =0V	250			V	
Drain-Source Leakage Current	I _{DSS}	V _{DS} =250V, V _{GS} =0V			1	μA	
Forwar	rd	V _{GS} =+30V, V _{DS} =0V			+100	nA	
Gate-Source Leakage Current Revers	1000	V _{GS} =-30V, V _{DS} =0V			-100	nA	
ON CHARACTERISTICS							
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}$, $I_D=250\mu A$			4	V	
Static Drain-Source On-State Resistance	ce R _{DS(ON)}	V _{GS} =10V, I _D =7.5A		0.18	0.25	Ω	
DYNAMIC PARAMETERS							
Input Capacitance	C _{ISS}			830	1080	pF	
Output Capacitance	Coss	V_{GS} =0V, V_{DS} =25V, f=1.0MHz		200	260	pF	
Reverse Transfer Capacitance	C_{RSS}	<u>]</u>		25	33	pF	
SWITCHING PARAMETERS							
Total Gate Charge	Q_{G}			33	40	nC	
Gate to Source Charge	Q_GS	V _{GS} =10V, V _{DD} =120V, I _D =18A		6		nC	
Gate to Drain Charge	Q_GD			6.7		nC	
Turn-ON Delay Time	t _{D(ON)}	V_{DD} =30V, I_{D} =1A, R_{G} =25 Ω ,		23	35	ns	
Rise Time	t _R			50	74	ns	
Turn-OFF Delay Time	t _{D(OFF)}	V_{GS} =10V, R_L =30 Ω		314	332	ns	
Fall-Time	t _F			89	97	ns	
SOURCE- DRAIN DIODE RATINGS A	ND CHARACTE	RISTICS					
Maximum Body-Diode Continuous					4.5	^	
Current	I _S				15	Α	
Maximum Body-Diode Pulsed Current	I _{SM}				60	Α	
Drain-Source Diode Forward Voltage	V_{SD}	I _S =15A, V _{GS} =0V			1.5	V	
	TC W	I _S =15A, V _{GS} =0V					
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